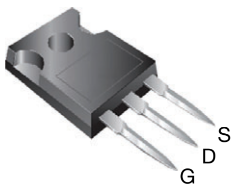
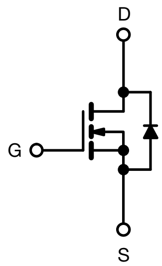
EF Series Power MOSFET With Fast Body Diode

TO-247AC





N-Channel MOSFET

FEATURES

- A specific on resistance (mΩ-cm^2) reduction of 25 %
- Low figure-of-merit (FOM) R_{on} x Q_g
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Renewable energy
  - Solar (PV inverters)

PRODUCT SUMMARY		
V_{DS} (V) at T_J max.	650	
$R_{DS(on)}$ typ. (Ω) at 25 °C	V_{GS} = 10 V	0.084
Q_g max. (nC)	134	
Q_{gs} (nC)	16	
Q_{gd} (nC)	48	
Configuration	Single	

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free and halogen-free	SiHG35N60EF-GE3

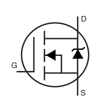
ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	600	V
Gate-source voltage			V_{GS}	± 30	V
Continuous drain current (T_J = 150 °C)	V_{GS} at 10 V	T_C = 25 °C	I_D	32	A
		T_C = 100 °C		20	
Pulsed drain current [a]			I_{DM}	80	A
Linear derating factor				2.0	W/°C
Single pulse avalanche energy [b]			E_{AS}	298	mJ
Maximum power dissipation			P_D	250	W
Operating junction and storage temperature range			T_J, T_{stg}	-55 to +150	°C
Drain-source voltage slope	T_J = 125 °C		dv/dt	100	V/ns
Reverse diode dv/dt [d]				50	
Soldering recommendations (peak temperature) [c]	For 10 s			260	°C

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature
b. V_{DD} = 140 V, starting T_J = 25 °C, L = 28.2 mH, R_g = 25 Ω, I_{AS} = 4.6 A
c. 1.6 mm from case
d. I_{SD} = 17 A, di/dt = 300 A/μs, starting T_J = 25 °C

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	0.5	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA	600	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 10 mA	-	0.66	-	V/°C
Gate-source threshold voltage (N)	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	2.0	-	4.0	V
Gate-source leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
		V_{GS} = ± 30 V	-	-	± 1	μA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 480 V, V_{GS} = 0 V	-	-	1	μA
		V_{DS} = 480 V, V_{GS} = 0 V, T_J = 125 °C	-	-	500	
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 17 A	-	0.084	0.097	Ω
Forward transconductance [a]	g_{fs}	V_{DS} = 30 V, I_D = 17 A	-	8	-	S
Dynamic						
Input capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 100 V, f = 1 MHz	-	2568	-	pF
Output capacitance	C_{oss}		-	113	-	
Reverse transfer capacitance	C_{rss}		-	7	-	
Effective output capacitance, energy related [a]	$C_{o(er)}$	V_{DS} = 0 V to 480 V, V_{GS} = 0 V	-	81	-	
Effective output capacitance, time related [b]	$C_{o(tr)}$		-	421	-	
Total gate charge	Q_g	V_{GS} = 10 V, I_D = 17 A, V_{DS} = 480 V	-	89	134	nC
Gate-source charge	Q_{gs}		-	16	-	
Gate-drain charge	Q_{gd}		-	48	-	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 480 V, I_D = 17 A, V_{GS} = 10 V, R_g = 9.1 Ω	-	28	56	ns
Rise time	t_r		-	85	170	
Turn-off delay time	$t_{d(off)}$		-	96	192	
Fall time	t_f		-	61	122	
Gate input resistance	R_g	f = 1 MHz, open drain	0.2	0.5	1.0	Ω
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	32	A
Pulsed diode forward current	I_{SM}		-	-	80	
Diode forward voltage	V_{SD}	T_J = 25 °C, I_S = 17 A, V_{GS} = 0 V	-	-	1.2	V
Reverse recovery time	t_{rr}	T_J = 25 °C, I_F = I_S = 17 A, di/dt = 100 A/μs, V_R = 400 V	-	150	300	ns
Reverse recovery charge	Q_{rr}		-	1.1	2.2	μC
Reverse recovery current	I_{RRM}		-	14	-	A

Notes

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

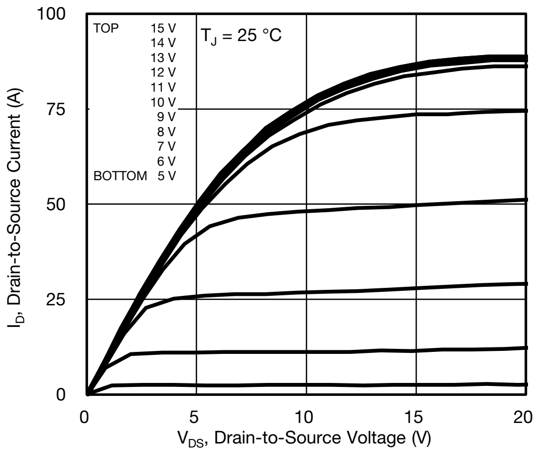


Fig. 1 - Typical Output Characteristics

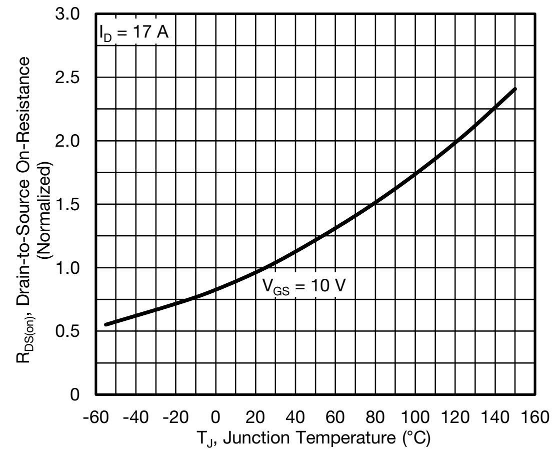


Fig. 4 - Normalized On-Resistance vs. Temperature

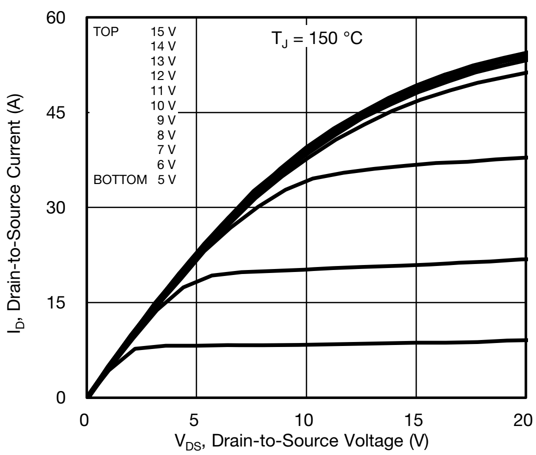


Fig. 2 - Typical Output Characteristics

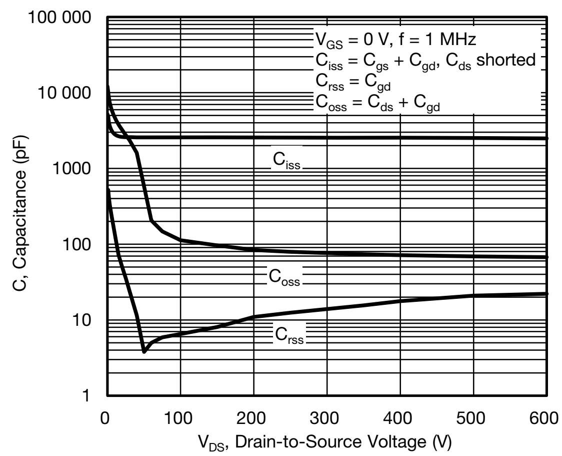


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

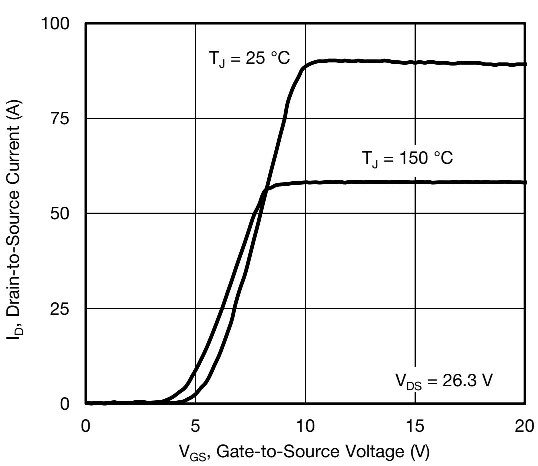


Fig. 3 - Typical Transfer Characteristics

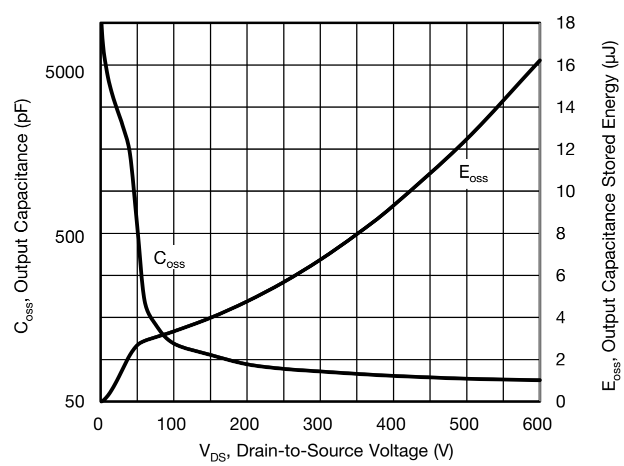


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

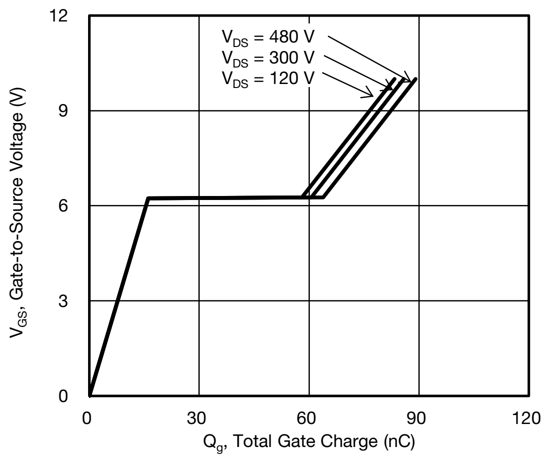


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

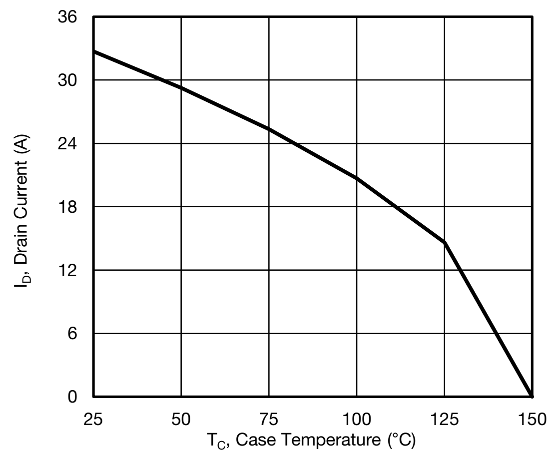


Fig. 10 - Maximum Drain Current vs. Case Temperature

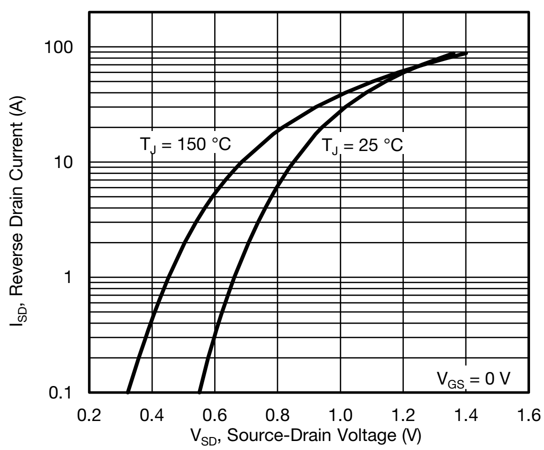


Fig. 8 - Typical Source-Drain Diode Forward Voltage

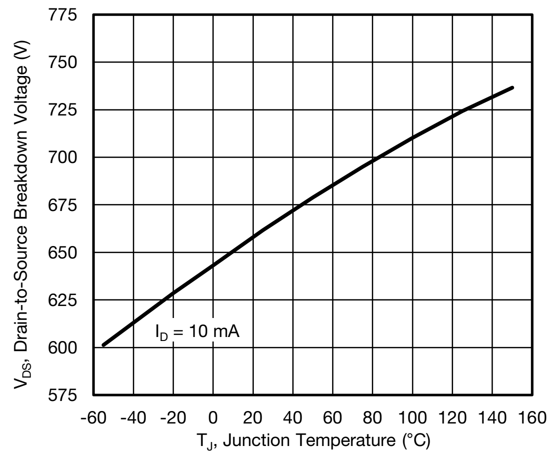
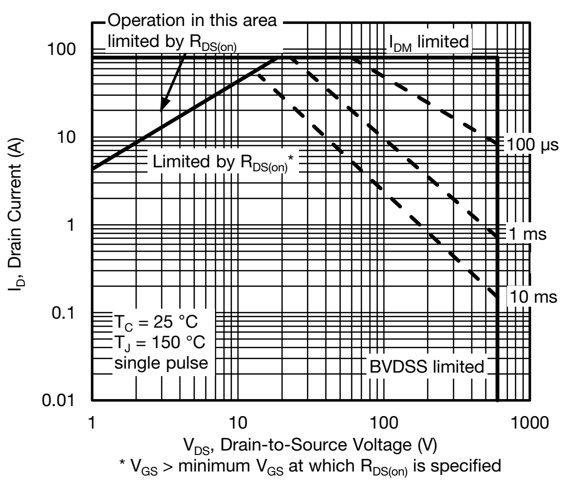


Fig. 11 - Temperature vs. Drain-to-Source Voltage



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Fig. 9 - Maximum Safe Operating Area

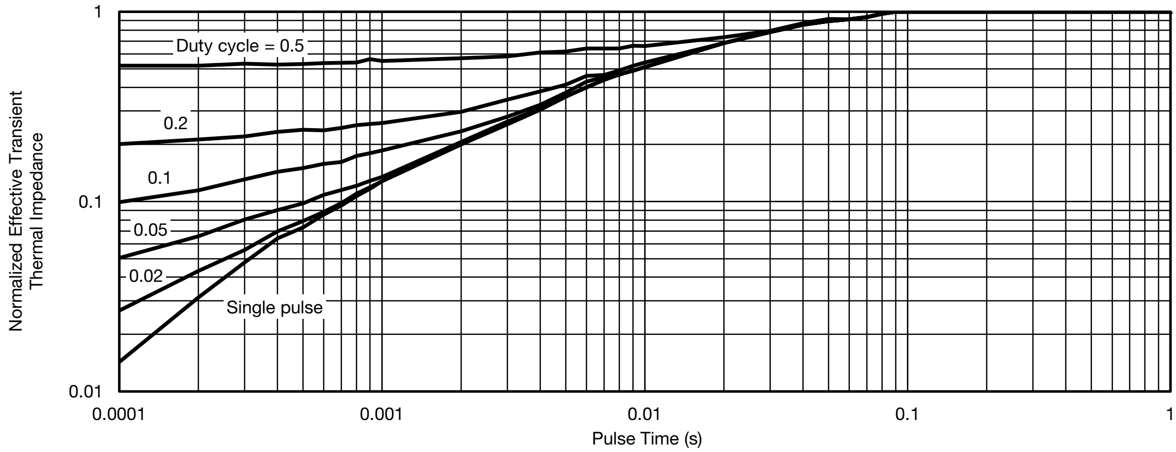


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case

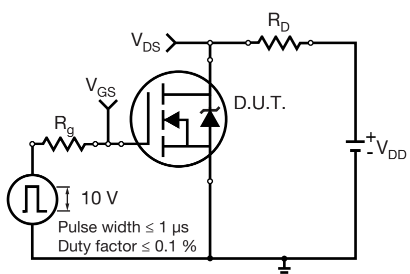


Fig. 13 - Switching Time Test Circuit

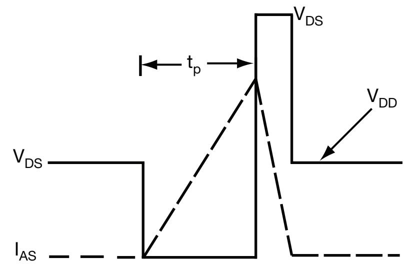


Fig. 16 - Unclamped Inductive Waveforms

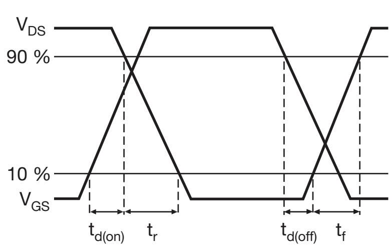


Fig. 14 - Switching Time Waveforms

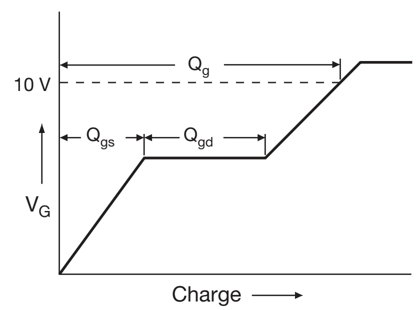


Fig. 17 - Basic Gate Charge Waveform

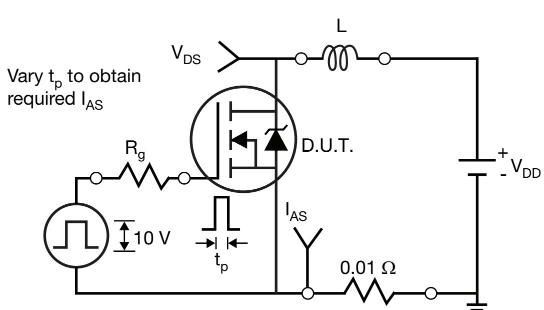


Fig. 15 - Unclamped Inductive Test Circuit

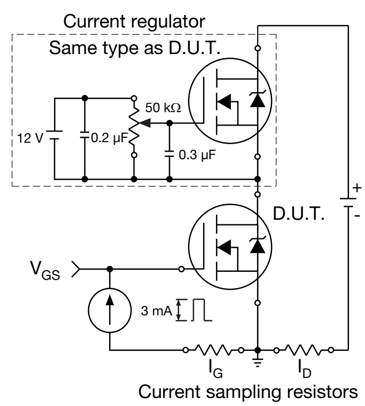
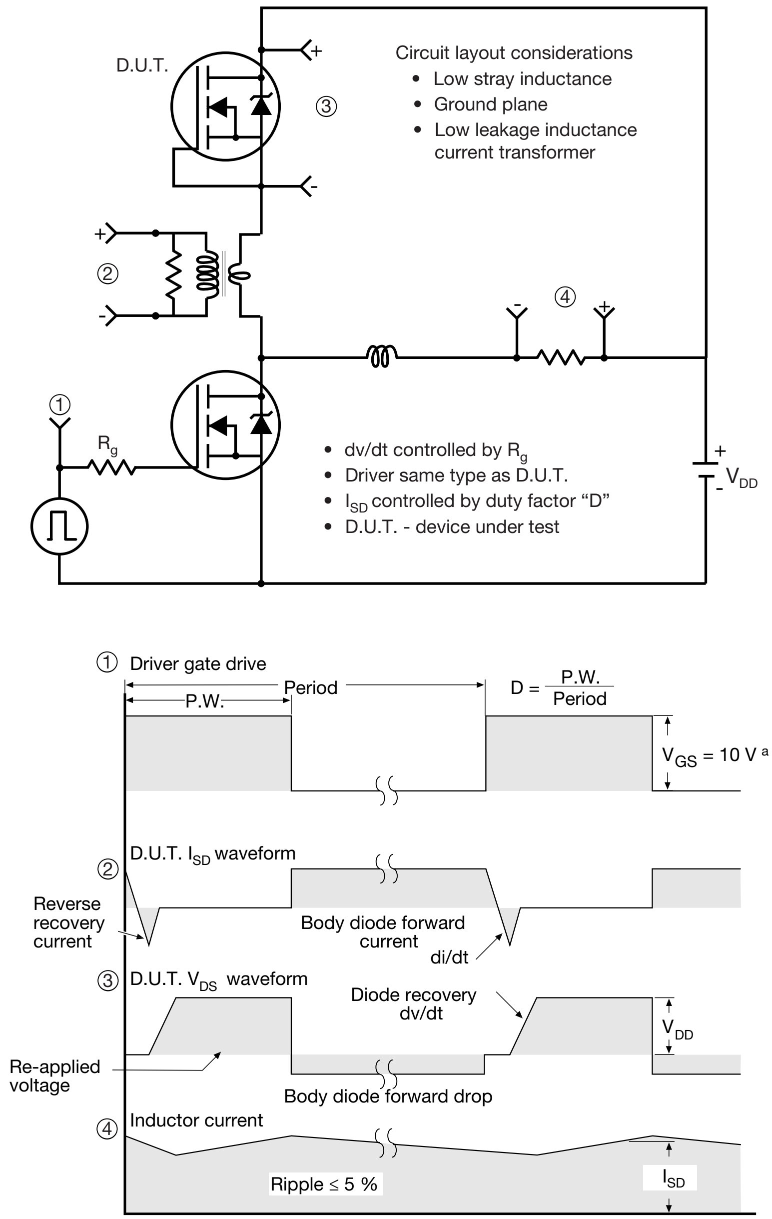


Fig. 18 - Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



Note

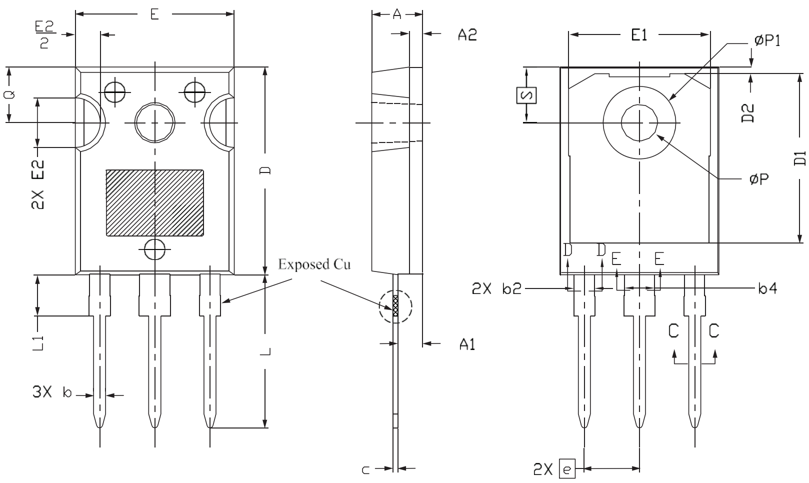
a. V_{GS} = 5 V for logic level devices

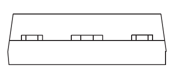
Fig. 19 - For N-Channel

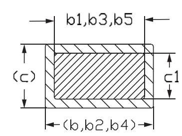
Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?92109.

TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C,D--D,E--E

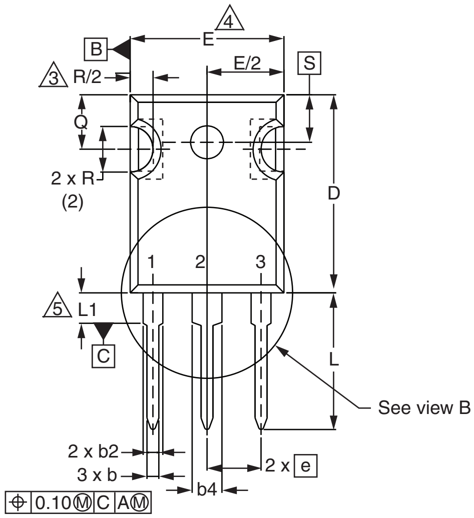
	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	NOTES
A	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.17	1.27	1.37	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
c	0.40	0.50	0.60	6
c1	0.40	0.50	0.56	
D	20.40	20.55	20.70	4

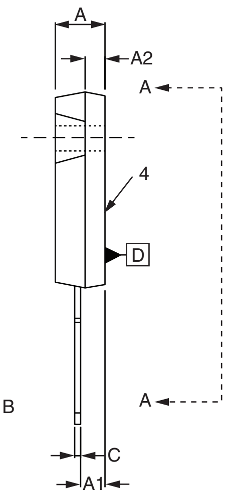
	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
E	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
e	5.46 BSC			
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
Ø P	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S	5.51 BSC			

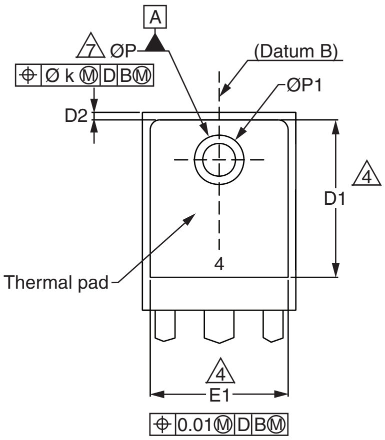
Notes

(1) Package reference: JEDEC® TO247, variation AC
(2) All dimensions are in mm
(3) Slot required, notch may be rounded
(4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
(5) Thermal pad contour optional with dimensions D1 and E1
(6) Lead finish uncontrolled in L1
(7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
(8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

VERSION 2: FACILITY CODE = Y

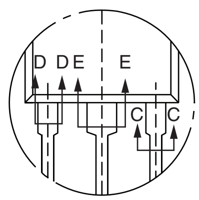




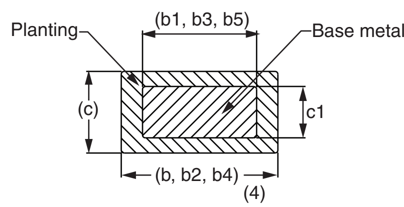


View A - A

Lead Assignments
1. Gate
2. Drain
3. Source
4. Drain



View B



Section C - C, D - D, E - E

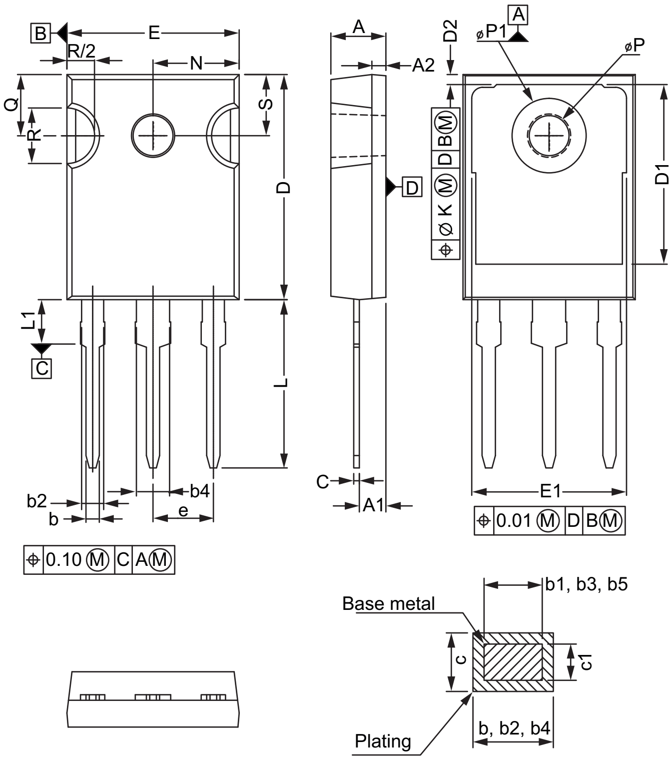
	MILLIMETERS		
DIM.	**MIN.**	**MAX.**	**NOTES**
A	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
c	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIMETERS		
DIM.	**MIN.**	**MAX.**	**NOTES**
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
e	5.46 BSC		
Ø k	0.254		
L	14.20	16.25	
L1	3.71	4.29	
Ø P	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

Notes

(1) Dimensioning and tolerancing per ASME Y14.5M-1994
(2) Contour of slot optional
(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
(4) Thermal pad contour optional with dimensions D1 and E1
(5) Lead finish uncontrolled in L1
(6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
(7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

VERSION 3: FACILITY CODE = N



	MILLIMETERS	
DIM.	**MIN.**	**MAX.**
A	4.65	5.31
A1	2.21	2.59
A2	1.17	1.37
b	0.99	1.40
b1	0.99	1.35
b2	1.65	2.39
b3	1.65	2.34
b4	2.59	3.43
b5	2.59	3.38
c	0.38	0.89
c1	0.38	0.84
D	19.71	20.70
D1	13.08	-

	MILLIMETERS	
DIM.	**MIN.**	**MAX.**
D2	0.51	1.35
E	15.29	15.87
E1	13.46	-
e	5.46 BSC	
k	0.254	
L	14.20	16.10
L1	3.71	4.29
N	7.62 BSC	
P	3.56	3.66
P1	-	7.39
Q	5.31	5.69
R	4.52	5.49
S	5.51 BSC	

ECN: E22-0452-Rev. G, 31-Oct-2022
DWG: 5971

Notes
(1) Dimensioning and tolerancing per ASME Y14.5M-1994
(2) Contour of slot optional
(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
(4) Thermal pad contour optional with dimensions D1 and E1
(5) Lead finish uncontrolled in L1
(6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

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